

CMOS Latched 4/8 Channel Analog Multiplexers

ADG528A/ADG529A

FEATURES

44V Supply Maximum Rating
V_{SS} to V_{DD} Analog Signal Range
Single/Dual Supply Specifications
Wide Supply Ranges (10.8V to 16.5V)
Microprocessor Compatible (100ns WR Pulse)
Extended Plastic Temperature Range
(-40°C to +85°C)
Low Leakage (20pA typ)
Low Power Dissipation (28mW max)
Available in 16-Lead DIP and
20-Lead LCCC/PLCC Packages
Superior Alternative to:
DG528
DG529

GENERAL DESCRIPTION

The ADG528A and ADG529A are CMOS monolithic analog multiplexers with 8 channels and dual 4 channels respectively. On-chip latches facilitate microprocessor interfacing. The ADG528A switches one of 8 inputs to a common output depending on the state of three binary addresses and an enable input. The ADG529A switches one of 4 differential inputs to a common differential output depending on the state of two binary addresses and an enable input. Both devices have TTL and 5V CMOS logic compatible digital inputs.

The ADG528A and ADG529A are designed on an enhanced LC2MOS process which gives an increased signal capability of $V_{\rm SS}$ to $V_{\rm DD}$ and enables operation over a wide range of supply voltages. The devices can comfortably operate anywhere in the 10.8V to 16.5V single or dual supply range. These multiplexers also feature high switching speeds and low $R_{\rm ON}$.

PRODUCT HIGHLIGHTS

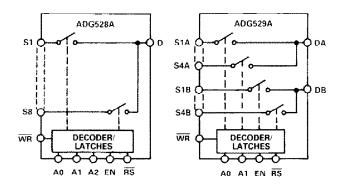
- Single/Dual Supply Specifications with a Wide Tolerance: The devices are specified in the 10.8V to 16.5V range for both single and dual supplies.
- 2. Easily Interfaced:

The ADG528A and ADG529A can be easily interfaced with microprocessors. The \overline{WR} signal latches the state of the address control lines and the enable line. The \overline{RS} signal clears both the address and enable data in the latches resulting in no output (all switches off). \overline{RS} can be tied to the microprocessor reset pin.

REV. A

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FUNCTIONAL BLOCK DIAGRAMS



3. Extended Signal Range:

The enhanced LC²MOS processing results in a high breakdown and an increased analog signal range of V_{SS} to V_{DD} .

- Break-Before-Make Switching: Switches are guaranteed break-before-make so that input signals are protected against momentary shorting.
- 5. Low Leakage:

Leakage currents in the range of 20pA make these multiplexers suitable for high precision circuits.

ORDERING GUIDE

Model ¹	Temperature Range	Package Option ²
ADG528AKN	-40°C to +85°C	N-28
ADG528AKP	-40°C to +85°C	P-20A
ADG528ABQ	-40°C to +85°C	Q-18
ADG528ATQ ³	-55°C to +125°C	Q-18
ADG528ATE ³	-55°C to +125°C	E-20A
ADG529AKN	-40°C to +85°C	N-18
ADG529AKP	-40°C to +85°C	P-20A
ADG529ABQ	-40°C to +85°C	Q-18
ADG529ATQ ³	-55°C to +125°C	Q-18
ADG529ATE ³	−55°C to +125°C	E-20A

NOTES

To order MIL-STD-883, Class B processed parts, add /883B to part number. See Analog Devices Military Products Databook (1990) for military data sheet.

E = Leadless Ceramic Chip Carrier (LCCC); N = Plastic DIP; P = Plastic Leaded Chip Carrier (PLCC); Q = Cerdip.

One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A.
Tel: 617/329-4700 Fax: 617/326-8703 Twx: 710/394-6577
Telex: 924491 Cable: ANALOG NORWOODMASS

ADG528A/ADG529A — SPECIFICATIONS

Dual Supply ($v_{pp} = +10.8V$ to +16.5V, $v_{ss} = -10.8V$ to -16.5V unless otherwise noted.)

	ADG ADG K Ve	529A	ADO	9528A 9529A ersion	ADG	G528A G529A ersion		
Parameter	+ 25°C	−40°C to +85°C	+25°C	– 40°C to + 85°C	+25°C	-55°C to +125°C	Units	Comments
ANALOG SWITCH								
Analog Signal Range	V _{SS} V _{DD}	$\begin{matrix} v_{ss} \\ v_{\rm DD} \end{matrix}$	V _{SS} V _{DD}	$v_{ss} \\ v_{dd}$	V _{SS} V _{DD}	$v_{ss} \ v_{dd}$	V min V max	
R _{ON}	280 450	600	280 450	600	280 450	600	Ωtyp Ωmax	- 10V ≤ V _S ≤ + 10V, I _{DS} = 1mA; Test Circuit I
R _{ON} Drift	300 0.6	400	300 0.6	400	300 0.6	400	Ω max Ω max %/°C typ	$\begin{split} V_{DD} &= 15V(\pm 10\%), V_{SS} = -15V(\pm 10\%) \\ V_{DD} &= 15V(\pm 5\%), V_{SS} = -15V(\pm 5\%) \\ &- 10V \leqslant V_{S} \leqslant +10V, I_{DS} = 1\text{mA} \end{split}$
R _{ON} Match	5		5		5		%typ	$-10V \leq V_{S} \leq +10V, I_{DS} = 1 \text{mA}$
I _S (OFF), Off Input Leakage	0.02 1	50	0.02	50	0.02 1	50	nA typ nA max	$V1 = \pm 10V$, $V2 = \mp 10V$; Test Circuit 2
1 _D (OFF), Off Output Leakage ADG528A ADG529A	0.04 1 1	100 50	0.04 1 1	100 50	0.04 1 1	100 50	nA typ nA max nA max	V1 = ± 10V, V2 = ∓10V; Test Circuit 3
I _D (ON), On Channel Leakage ADG528A ADG529A	0.04 1 1	100 50	0.04 1 1	100 50	0.04 1 1	100 50	nA typ nA max nA max	$V1 = \pm 10V$, $V2 = \mp 10V$; Test Circuit 4
I _{DIFF} , Differential Off Output Leakage (ADG529A only)		25		25		25	nA max	V1 = ± 10V, V2 = ∓ 10V; Test Circuit 5
DIGITAL CONTROL V _{INH} , Input High Voltage V _{INL} , Input Low Voltage I _{INL} or I _{INH} C _{IN} Digital Input Capacitance	8	2.4 0.8 1	8	2.4 0.8 1	8	2.4 0.8 1	V min V max µA max pF max	V _{IN} =0 to V _{DD}
DYNAMIC CHARACTERISTICS ¹	+		l'		-	***************************************	F1 1134	
TRANSITION TRANSITION	200 300	400	200 300	400	200 300	400	ns typ ns max	$V1 = \pm 10V$, $V2 = \mp 10V$; Test Circuit 6
COPEN	50 25	10	50 25	10	50 25	10	ns typ ns min	Test Circuit 7
$t_{ON}(EN,\overline{WR})$	200 300	400	200 300	400	200 300	400	ns typ ns max	Test Circuits 8 and 9
$t_{OFF}(EN, \overline{RS})$	200 300	400	200 300	400	200 300	400	ns typ ns max	Test Circuits 8 and 10
tw Write Pulse Width ts Address, Enable Setup Time tH Address, Enable Hold Time tRS Reset Pulse Width	100	120 100 10 100	100	120 100 10 100	100	130 100 10 10	ns min ns min ns min ns min	See Figure 1 See Figure 1 See Figure 1 See Figure 2
OFF Isolation	68 50		68 50		68 50		dB typ dB min	$V_{EN} = 0.8V, R_L = 1k\Omega, C_L = 15pF,$ $V_S = 7V \text{ rms}, f = 100kHz$
C _S (OFF) C _D (OFF)	5		5		5		pF typ	$V_{EN} = 0.8V$
ADG528A ADG529A	22 11		22 11		22 11		pF typ pF typ	$V_{EN} = 0.8V$
Q _{INJ} , Charge Injection	4		4		4		pC typ	$R_S = 0\Omega$, $V_S = 0V$; Test Circuit 11
POWER SUPPLY I _{DD}	0.6	1.5	0.6	1.5	0.6	1.5	mA typ mA max	$V_{IN} = V_{INL}$ or V_{INH}
I _{SS}	20	0.2	20	0.2	20	0.2	μA typ mA max	$V_{IN} = V_{INL}$ or V_{INH}
Power Dissipation	10	28	10	28	10	28	mW typ	

NOTE 1 Sample tested at $+25^{\circ}$ C to ensure compliance.

Specifications subject to change without notice.

Single Supply ($V_{DD} = +10.8V \text{ to } +16.5V, V_{SS} = GND = DV \text{ unless otherwise noted.}$)

	ADG528A ADG529A K Version		ADG528A ADG529A B Version		ADG528A ADG529A T Version			
Parameter	+ 25°C	-40°C to +85°C	+25°C	– 40°C to + 85°C	+25°C	55°C to + 125°C	Units	Comments
ANALOG SWITCH								
Analog Signal Range	GND	GND	GND	GND	GND	GND	V min	
	VDD	V_{DD}	V_{DD}	V_{DD}	V_{DD}	$\mathbf{v}_{\mathtt{DD}}$	V max	
R _{ON}	500 700	1000	700	1000	500 700	1000	Ωtyp	$GND \le V_S \le +10V$, $I_{DS} = 0.5 \text{mA}$; Test Circuit 1
R _{ON} Drift	0.6	ITAN	0.6	1000	0.6	1000	Ωmax %/°Ctyp	$GND \le V_S \le + 10V$, $I_{DS} = 0.5mA$
R _{ON} Match	5		5		5		% typ	$GND \le V_S \le + 10V, I_{DS} = 0.5 \text{mA}$ $GND \le V_S \le + 10V, I_{DS} = 0.5 \text{mA}$
I _S (OFF), Off Input Leakage	0.02		0.02		0.02		nA typ	V1 = + 10V/GND, V2 = GND/ + 10V
13 (011), On input Demande	1	50	1	50	1	50	nA max	Test Circuit 2
ID (OFF), Off Output Leakage	0.04		0.04		0.04		nA typ	V1 = +10V/GND, V2 = GND/+10V
ADG528A	1	100	1	100	1	100	nA max	Test Circuit 3
ADG529A	1	50	1	50	i	50	nA max	a contraction of
ID (ON), On Channel Leakage	0.04		0.04		0.04		nA typ	VI = + 10V/GND, V2 = GND/ + 10V
ADG528A	1	100	1	100	1	100	nA max	Test Circuit 4
ADG529A	1	50	1	50	1	50	nA max	
I _{DIFF} , Differential Off Output								V1 = +10V/GND, V2 = GND/ + 10V
Leakage (ADG529A only)	ļ	25		25		25	nA max	Test Circuit 5.
DIGITAL CONTROL								
V _{INH} , Input High Voltage		2.4		2.4		2.4	V min	
V _{INL} , Input Low Voitage I _{INL} or I _{INH}		0.8		0.8		0.8 1	V max	V -0V
C _{IN} Digital Input Capacitance	8	•	8	•	8		μA max pF max	$V_{IN} = 0 \text{ to } V_{DD}$
DYNAMIC CHARACTERISTICS ¹					Ť		pr max	
TRANSITION	300		300		300		nstyp	V1 = +10V/GND, $V2 = GND/ + 10V$; Test Circuit
	450	600	450	600	450	600	ns max	The state of the s
topen	50		50		50		ns typ	Test Circuit 7
	25	10	25	10	25	10	ns min	
$t_{ON}(EN,\overline{WR})$	250		250		250		ns typ	Test Circuits 8 and 9
	450	600	450	600	450	600	ns max	Total Calcard Called >
toff (EN, RS)	250		250		250		ns typ	Test Circuits 8 and 10
	450	600	450	600	450	600	ns max	A doc distance of the Lo
tw Write Pulse Width	100	120	100	120	100	130	ns min	See Figure 1
ts Address, Enable Setup Time		100		100		100	ns min	See Figure 1
t _H Address, Enable Hold Time t _{RS} Reset Pulse Width		10		10	ĺ	10	nsmin	See Figure 1
K-K/		100		100		100	ns min	See Figure 2
OFF Isolation	68 50		68	·	68		dB typ	$V_{EN} = 0.8V, R_L = 1k\Omega, C_L = 15pF,$
C (OPP)			50		50		dB min	$V_S = 3.5 \text{V rms}, f = 100 \text{kHz}$
C _S (OFF) C _D (OFF)	5		5		5		pF typ	$V_{EN} = 0.8V$
ADG528A	22		22		22		pF typ	$V_{EN} = 0.8V$
ADG529A Q _{IND} Charge Injection	11 4		11		11		pF typ	B = 00 V = 0V T-+C (2.1)
OWER SUPPLY	_		-		4	-	pC typ	$R_S = 0\Omega, V_S = 0V$; Test Circuit 11
OWER SUPPLY	0.6		0.6		۸,		\$	T) 42 . t/
*DD	0.0	1.5	0.0	1.5	0.6	1.5	mA typ mA max	$V_{IN} = V_{INL}$ or V_{INH}
Power Discipation	,,	1.2	,,	1.0		1.3		
Power Dissipation	11	25	11	25	11	25	mW typ	
		•-		رء		43	mW max	

NOTE Sample tested at +25°C to ensure compliance. Specifications subject to change without notice.

-3-REV. A

ABSOLUTE MAXIMUM RATINGS*

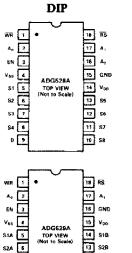
$(T_A = +25^{\circ}C \text{ unless otherwise noted})$	Digital Inputs ¹
	Voltage at A, EN, \overline{WR} , \overline{RS} V_{SS} - 4V to
V_{DD} to V_{SS} ,	$V_{DD} + 4V \text{ or}$
V_{DD} to GND	20mA, Whichever Occurs First
V_{SS} to GND	Power Dissipation (Any Package)
Analog Inputs ¹	Up to $+75^{\circ}$ C 470mW
Voltage at S, D V_{SS} – 2V to	Derates above +75°C by 6mW/°C
$V_{DD} + 2V \text{ or}$	Operating Temperature
20mA, Whichever Occurs First	Commercial (K Version)40°C to +85°C
Continuous Current, S or D	Industrial (B Version)40°C to +85°C
Pulsed Current S or D	Extended (T Version)55°C to +125°C
1ms Duration, 10% Duty Cycle 40mA	Storage Temperature Range65°C to +150°C
NOTE	Lead Temperature (Soldering, 10sec) + 300°C

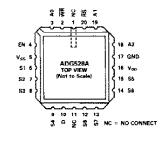
CAUTION

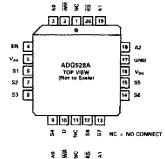
ESD (electrostatic discharge) sensitive device. The digital control inputs are diode protected; however, permanent damage may occur on unconnected devices subject to high energy electrostatic fields. Unused devices must be stored in conductive foam or shunts. The protective foam should be discharged to the destination socket before devices are removed.



PIN CONFIGURATIONS LCCC





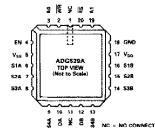


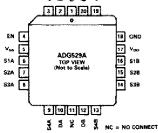
PLCC



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54A B





TRUTH TABLES

A	12	Al	A0	EN	WR	RS	ON SWITCH PAIR
X	(X	X	X	5	1	Retains Previous Switch Condition
2	(Х	Х	X.	Х	0	NONE (Address and Enable
1							Latches Cleared)
3	(X	Х	0	0	ı	NONE
0		0	0	1	0	1	1
0		0	1	1	0	1	2
0		1	0	1	0	1	3
0		1	1	1	0	1	4
1		Ð	0	1	0	1	5
1		0	1	1	0	1	6
1	-	1	0	1	0	1	7
1		1	1	1	0	1	8
X	X = Don't Care ADG528A						BA

A1	A0	EN	WR	RS	ON SWITCH PAIR
X	X	Х	5	1	Retains Previous Switch Condition
X	X	X	X	0	NONE (Address and Enable
		9			Latches Cleared)
X	X	0	0	1	NONE
0	0	l	0	1	1
0	1] 1	0	1	2
1	0	1	0	1	3
1	1	1	0	ł	4
Щ	<u> </u>	1	Ц		

X = Don't Care

ADG529A

Overvoltage at A, EN, WR, RS, S or D will be clamped by diodes. Current should be limited to the maximum rating above.

^{*}COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TIMING DIAGRAMS

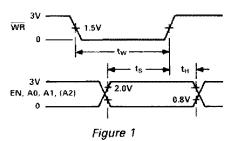


Figure 1 shows the timing sequence for latching the switch address and enable inputs. The latches are level sensitive; therefore, while \overline{WR} is held low, the latches are transparent and the switches respond to the address and enable inputs. This input data is latched on the rising edge of \overline{WR} .

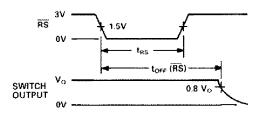


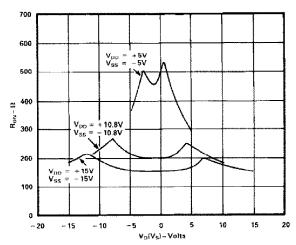
Figure 2

Figure 2 shows the Reset Pulse Width, t_{RS} , and Reset Turn-off Time, t_{OFF} (\overline{RS}).

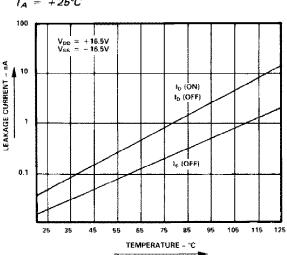
Note: All digital input signals rise and fall times measured from 10% to 90% of 3V. $t_R = t_F = 20 ns$.

Typical Performance Characteristics

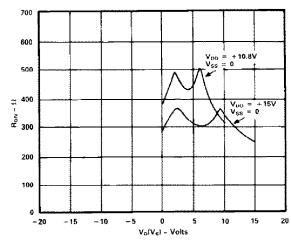
The multiplexers are guaranteed functional with reduced single or dual supplies down to 4.5V.



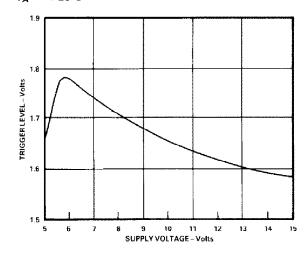
 R_{ON} as a Function of $V_D(V_S)$: Dual Supply Voltage,



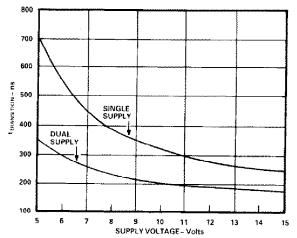
Leakage Current as a Function of Temperature (Note: Leakage Currents Reduce as the Supply Voltages Reduce)



 R_{ON} as a Function of $V_D(V_S)$: Single Supply Voltage, $T_A = +25^{\circ}C$

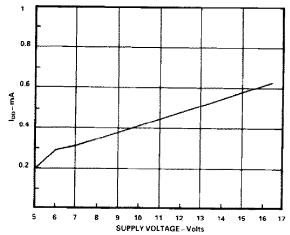


Trigger Levels vs. Power Supply Voltage, Dual or Single Supply, $T_A = +25^{\circ}C$



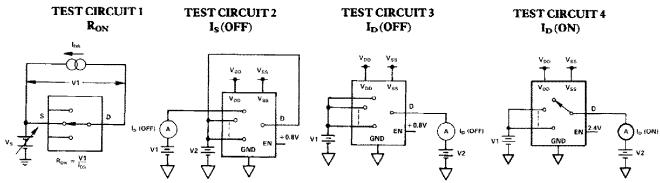
 $t_{TRANSITION}$ vs. Supply Voltage: Dual and Single Supplies, $T_A = +25^{\circ} C$

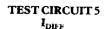
(Note: For V_{DD} and $|V_{SS}| < 10V$; $V1 = V_{DD}/V_{SS}$, $V2 = V_{SS}/V_{DD}$. See Test Circuit 6)

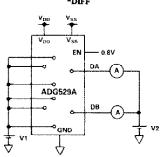


 I_{DD} vs. Supply Voltage: Dual or Single Supply, $T_A = +25^{\circ}C$

Test Circuits

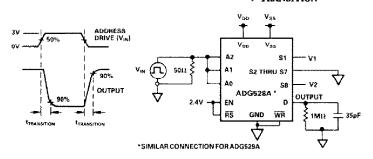




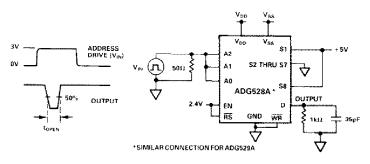


 $I_{DIFF} = I_{DA} (OFF) - I_{DB} (OFF)$

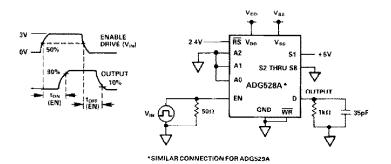
TEST CIRCUIT 6 SWITCHING TIME OF MULTIPLEXER, t_{TRANSITION}



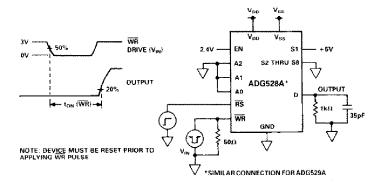
TEST CIRCUIT 7 BREAK-BEFORE-MAKE DELAY, topen



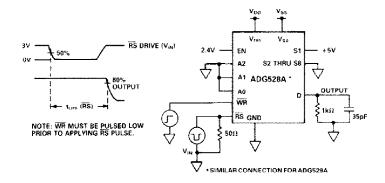
$\begin{array}{c} \textbf{TEST CIRCUIT 8} \\ \textbf{ENABLE DELAY}, t_{ON}(EN), t_{OFF}(EN) \end{array}$



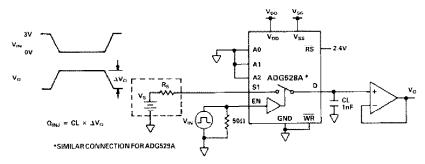
TEST CIRCUIT 9 WRITE TURN-ON TIME, $t_{ON}(\overline{WR})$



TEST CIRCUIT 10 RESET TURN-OFF TIME, $t_{OFF}(\overline{RS})$



TEST CIRCUIT 11 CHARGE INJECTION



TERMINOLO	OGY	t _{OFF} (EN)	Delay time between the 50% and 10% points of		
R _{ON} Match R _{ON} Drift I _S (OFF)	Ohmic resistance between terminals D and S Difference between the R _{ON} of any two channels Change in R _{ON} versus temperature Source terminal leakage current when the switch	^E TRANSITION	the digital input and switch "OFF" condition Delay time between the 50% and 90% points of the digital inputs and switch "ON" condition when switching from one address state to		
I_D (OFF)	is off Drain terminal leakage current when the switch is off Leakage current that flows from the closed switch	t _{OPEN}	another "OFF" time measured between 50% points of both switches when switching from one address state to another		
$V_{S}(V_{D})$	into the body Analog voltage on terminal S or D	V _{INL} V _{INH}	Maximum input voltage for Logic "0" Minimum input voltage for Logic "1"		
C _S (OFF) C _D (OFF) C _{IN} t _{ON} (EN)	Channel input capacitance for "OFF" condition Channel output capacitance for "OFF" condition Digital input capacitance Delay time between the 50% and 90% points of	I _{INL} (I _{INH}) V _{DD} V _{SS} I _{DD}	Input current of the digital input Most positive voltage supply Most negative voltage supply Positive supply current		
	the digital input and switch "ON" condition	I_{SS}	Negative supply current		

MECHANICAL INFORMATION OUTLINE DIMENSIONS

-8-

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